

FIG. 1

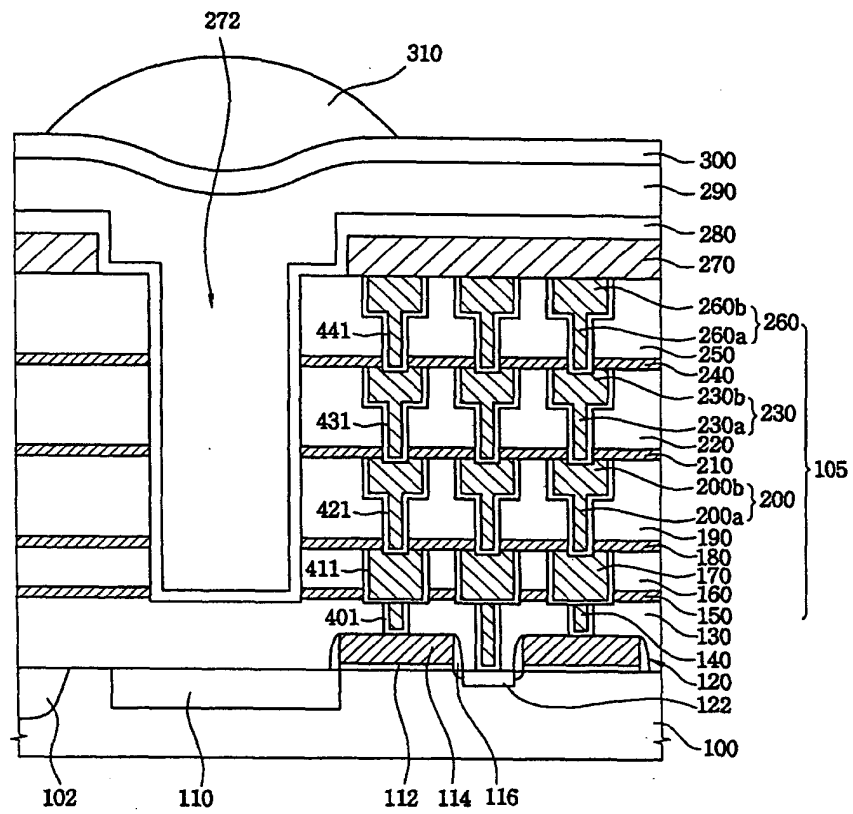


FIG. 2A

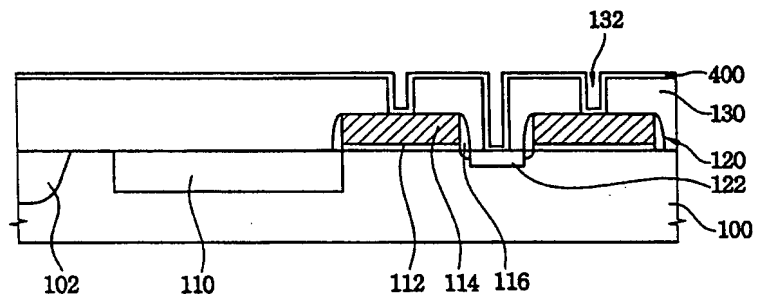


FIG. 2B

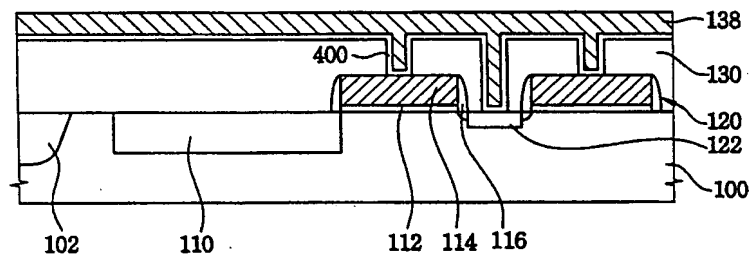


FIG. 2C

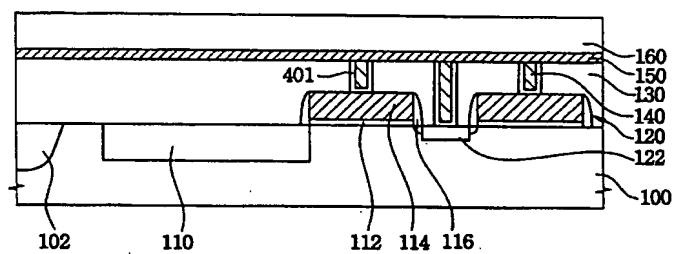


FIG. 2D

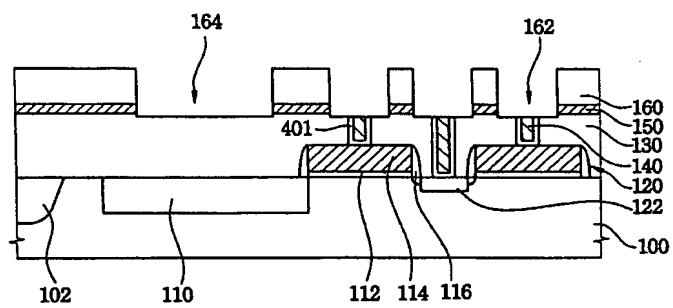


FIG. 2E

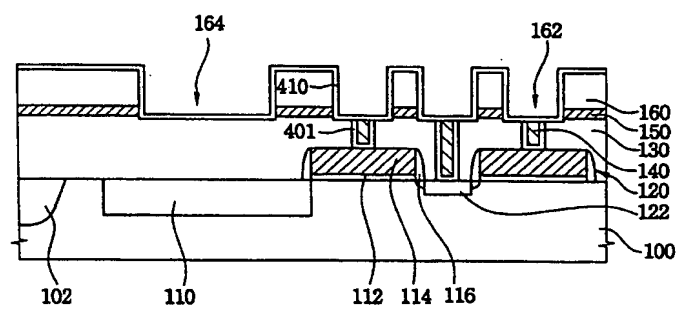


FIG. 2F

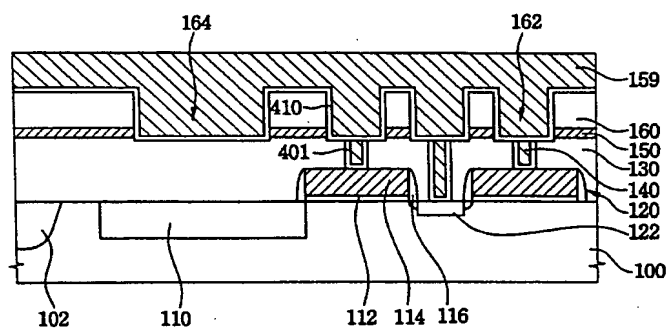


FIG. 2G

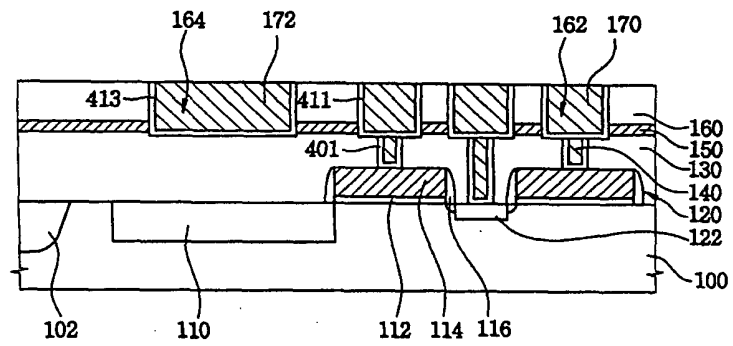


FIG. 2H

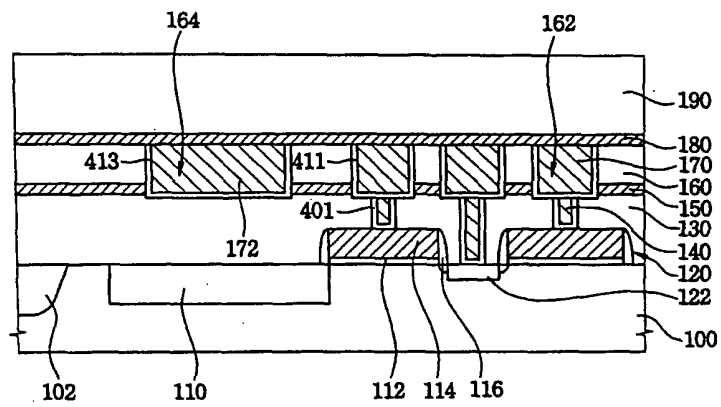


FIG. 2I

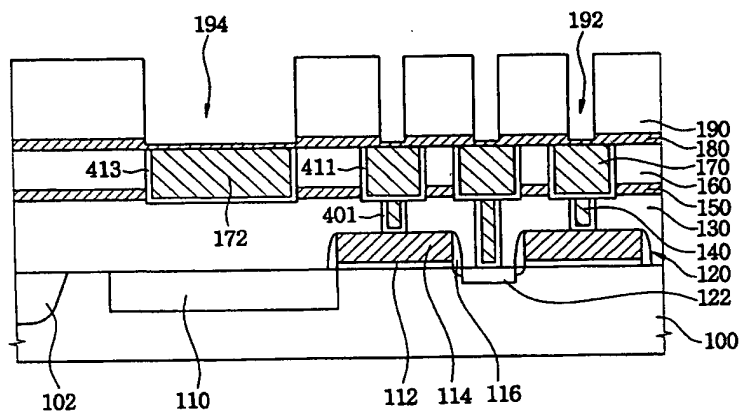


FIG. 2J

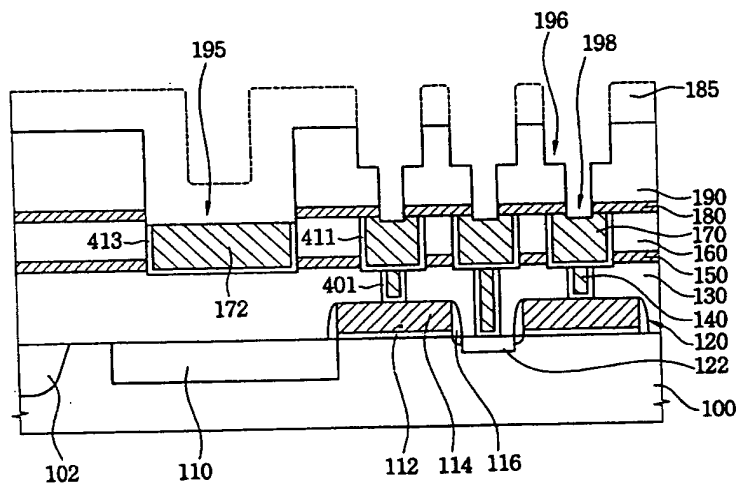


FIG. 2K

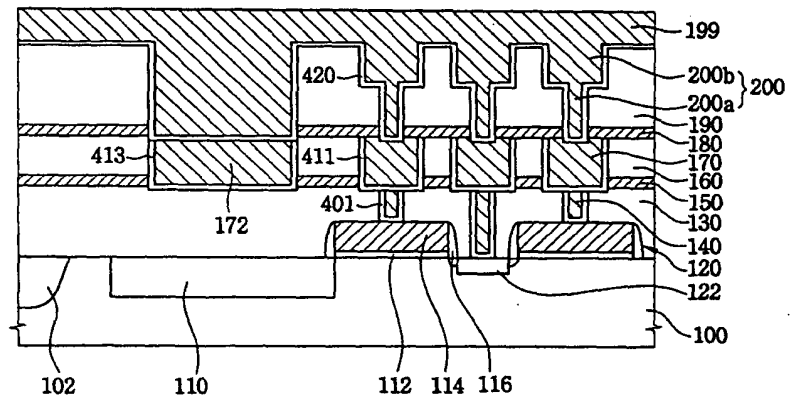


FIG. 2L

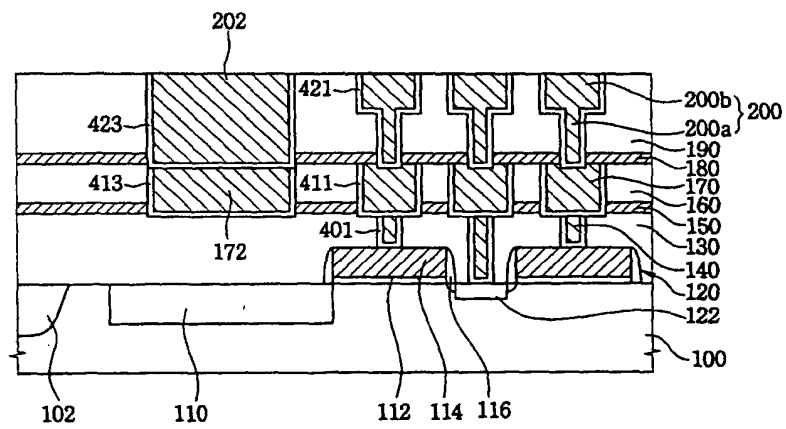


FIG. 2M

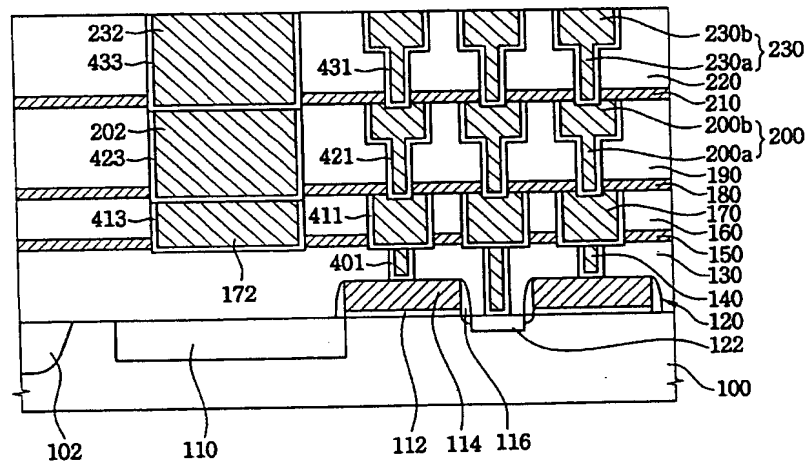




FIG. 2N

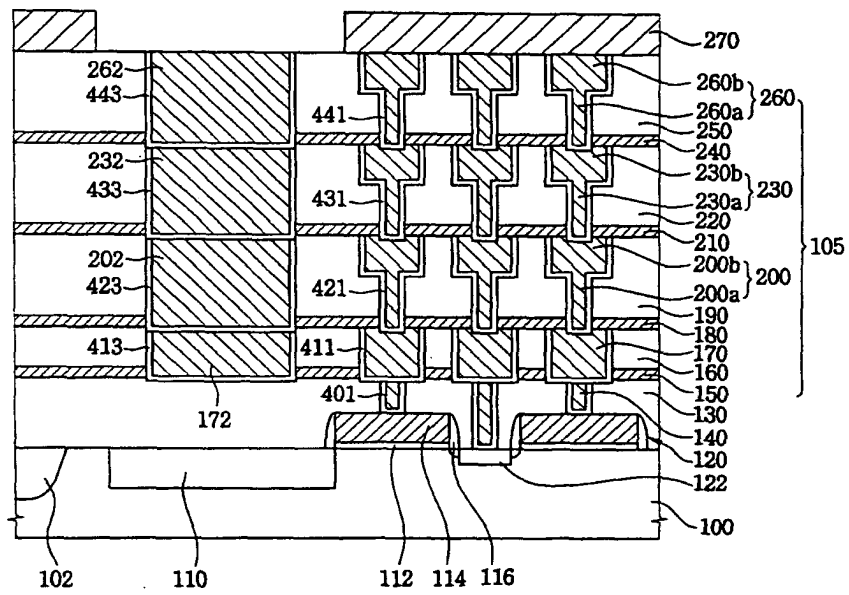


FIG. 20

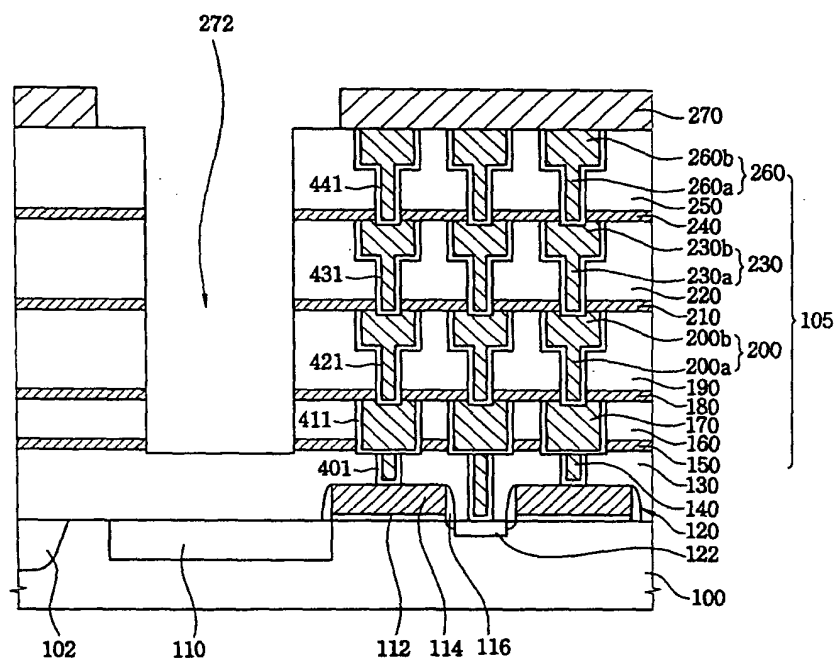


FIG. 2P

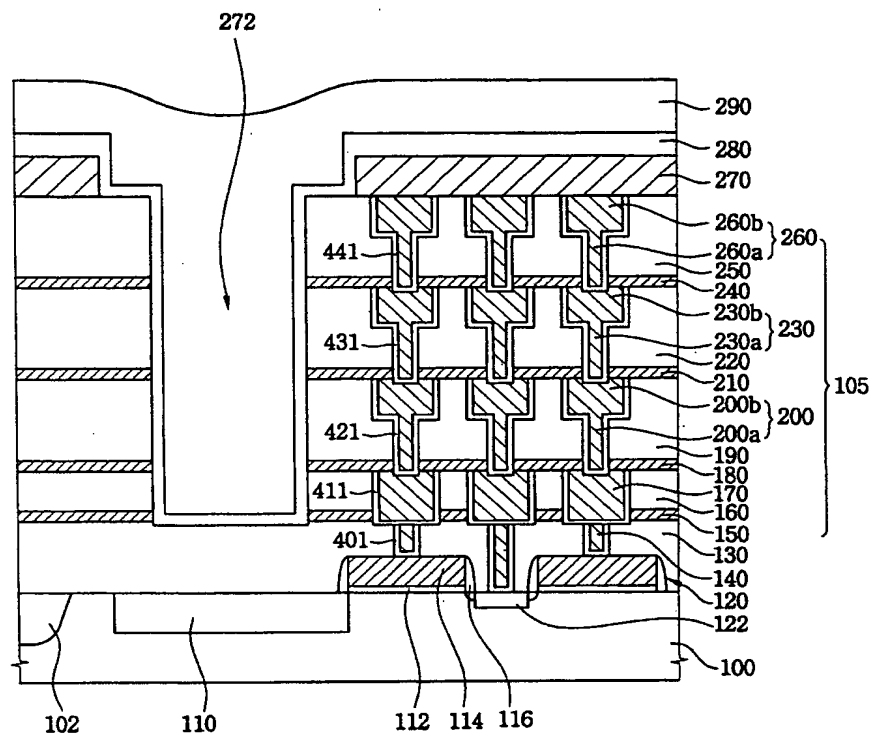


FIG. 2Q

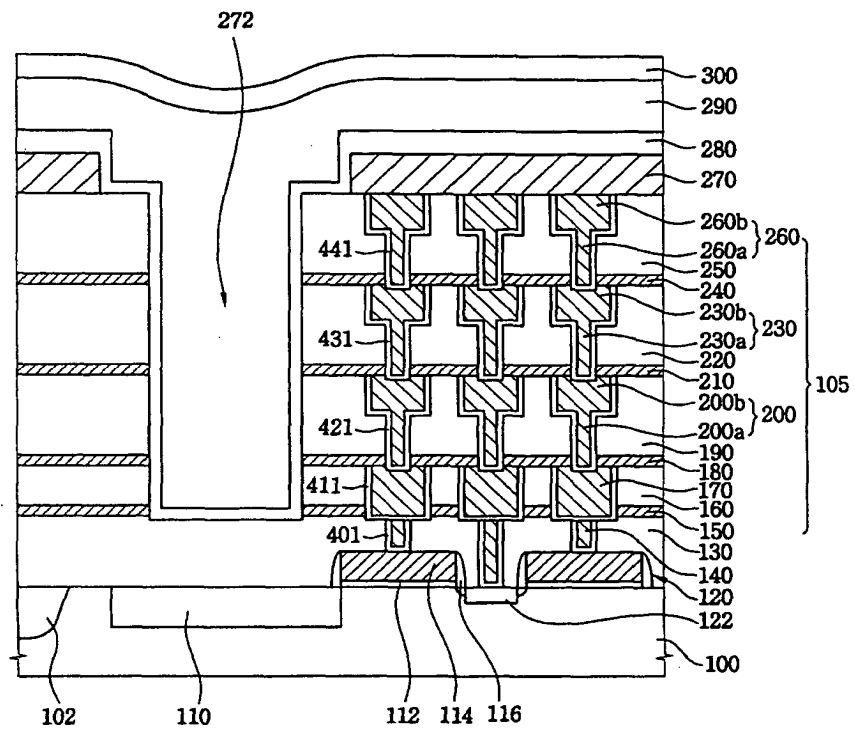


FIG. 2R

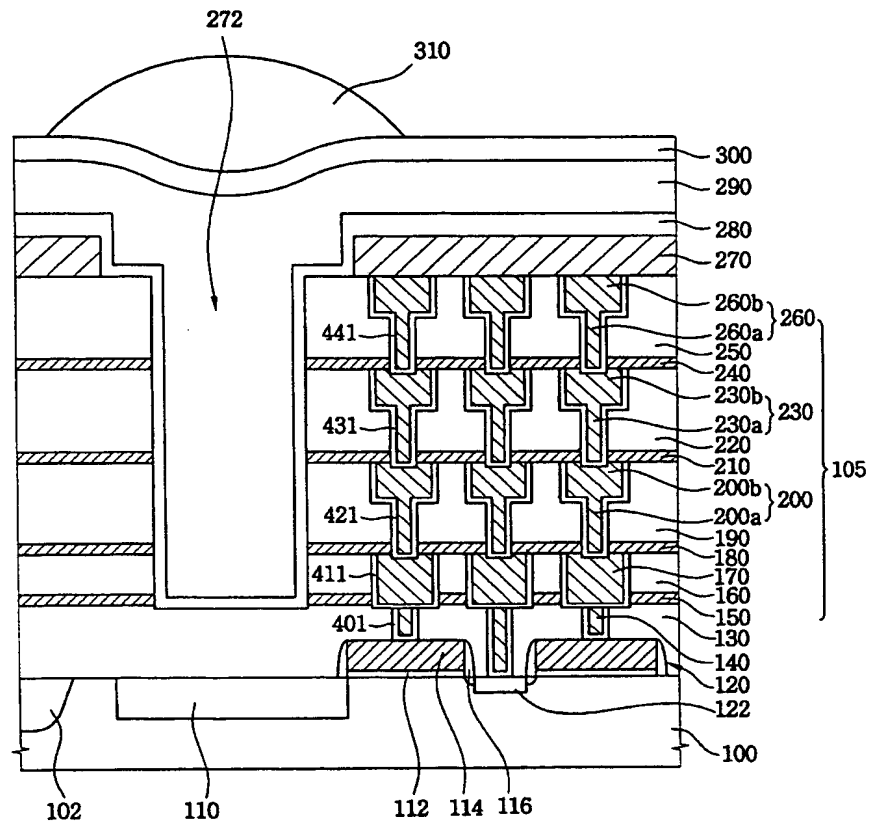


FIG. 3

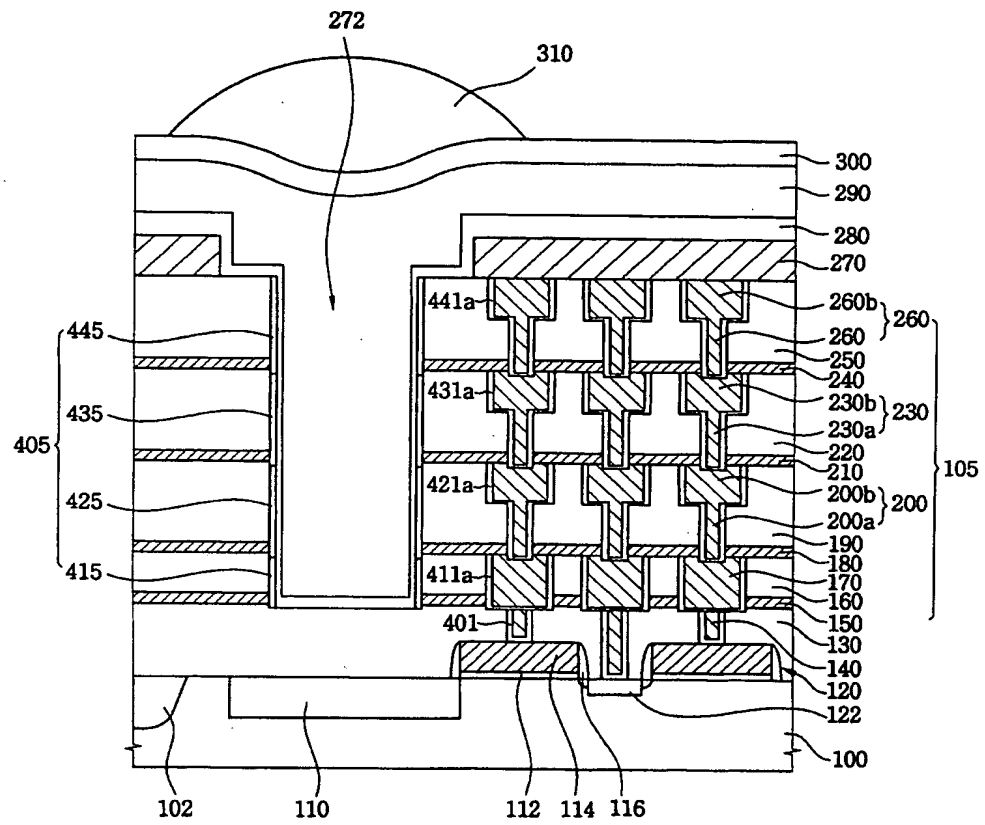


FIG. 4A

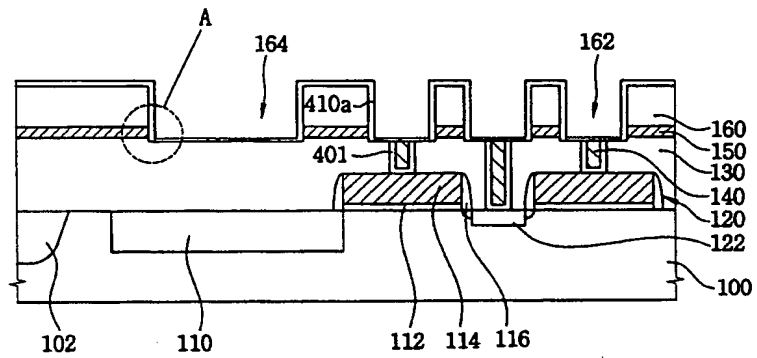
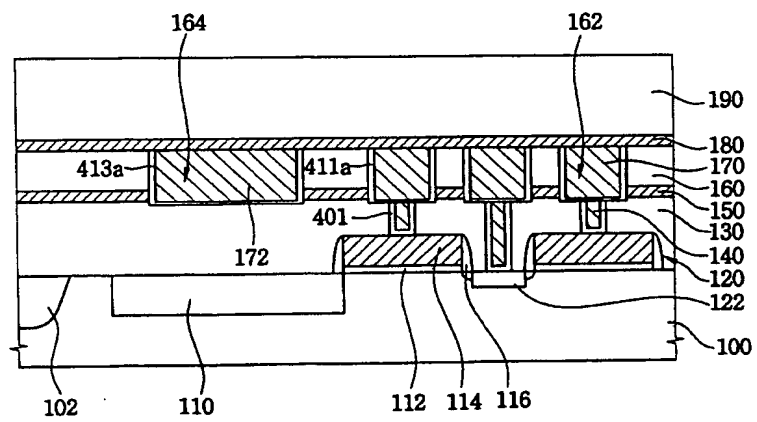


FIG. 4B



[illegible]

A cross-sectional diagram of a semiconductor device. The base layer is labeled 100. Above it are several horizontal layers: 102, 110, 122, 120, 140, 130, 150, 160, 170, 180, and 190. On top of these layers are various vertical structures. A central structure is labeled 303. To its right is another structure labeled 306. Further right is a structure labeled 308. At the far right is a structure labeled 304. Other labels include 190^n, 413a, 411a, 172, 401, 112, 114, and 116, which point to specific regions or features within the device structure.



FIG. 4E

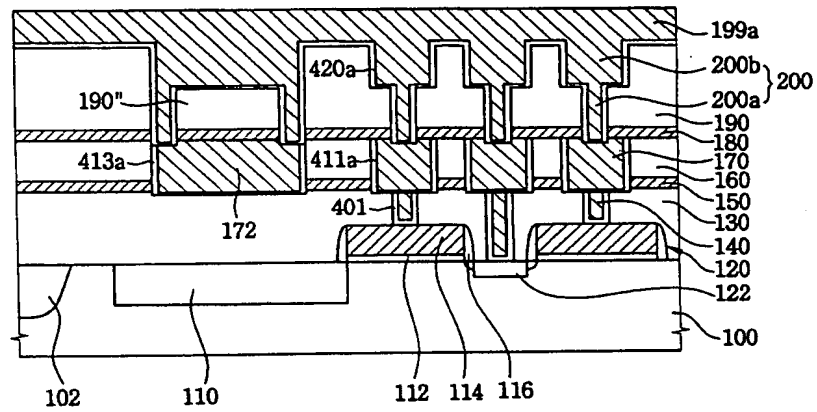


FIG. 4F

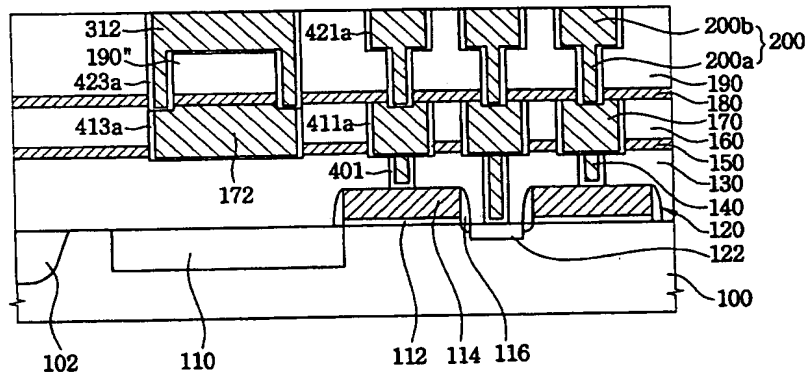


FIG. 4G

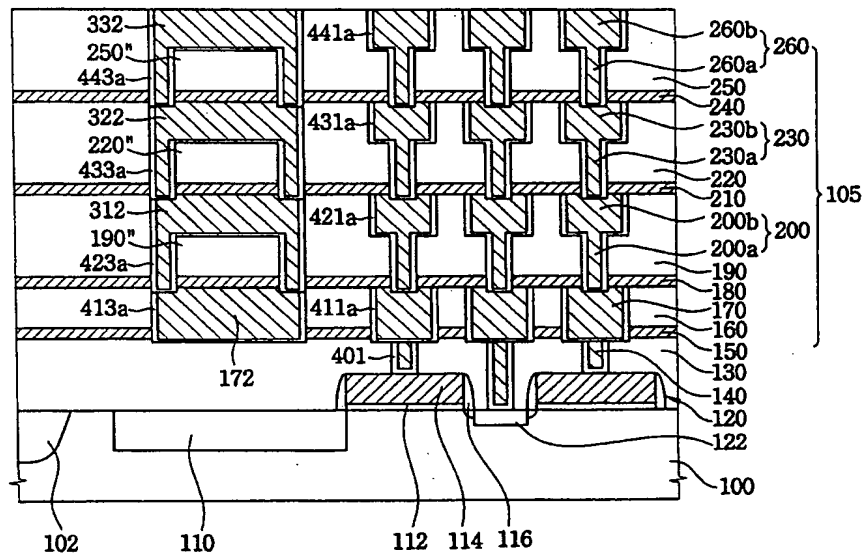


FIG. 4H

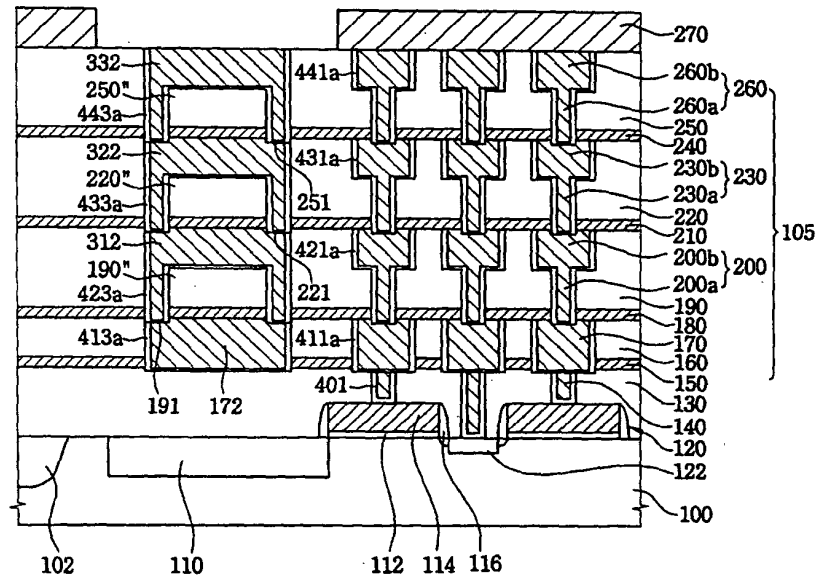


FIG. 4I

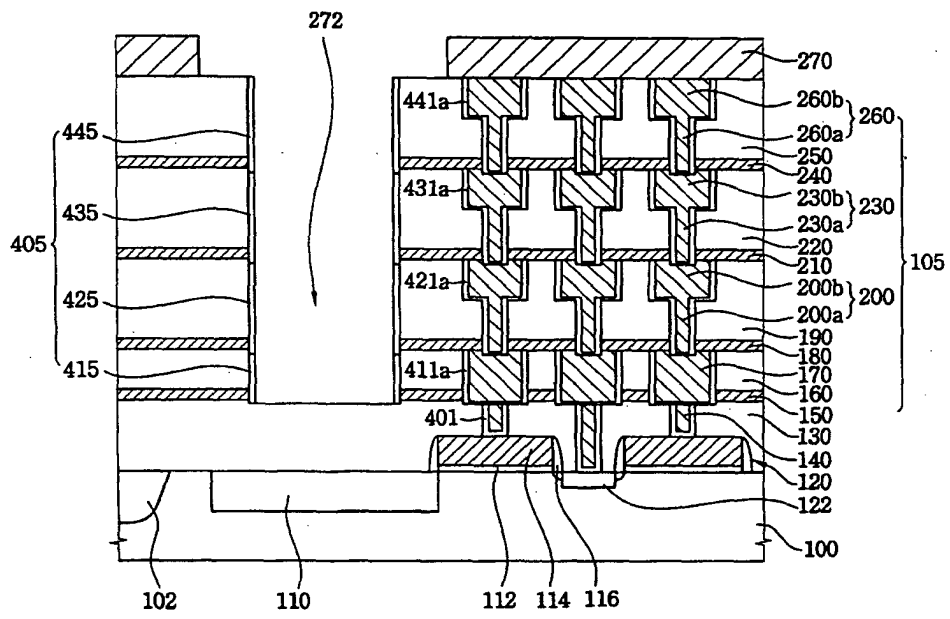


FIG. 4J

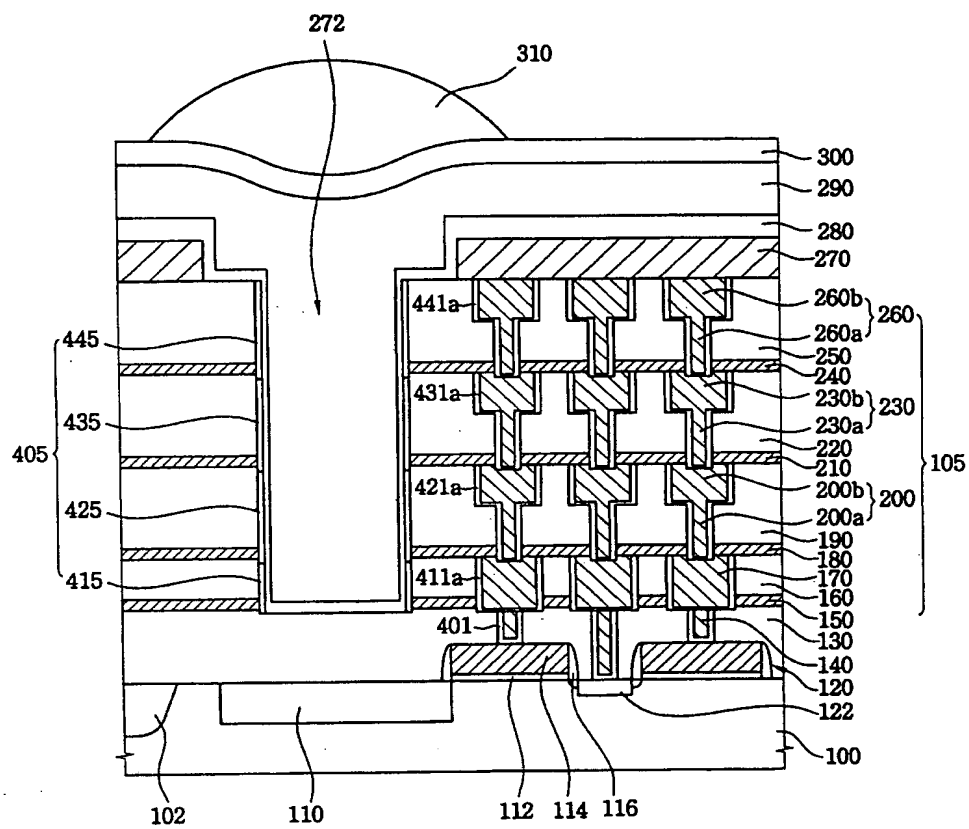


FIG. 5

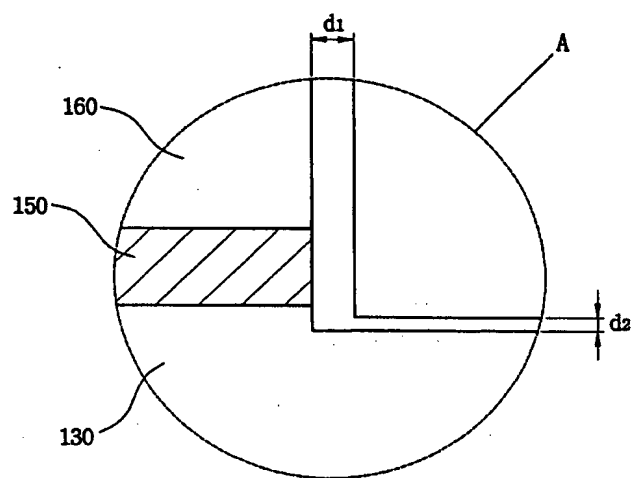


FIG. 6A

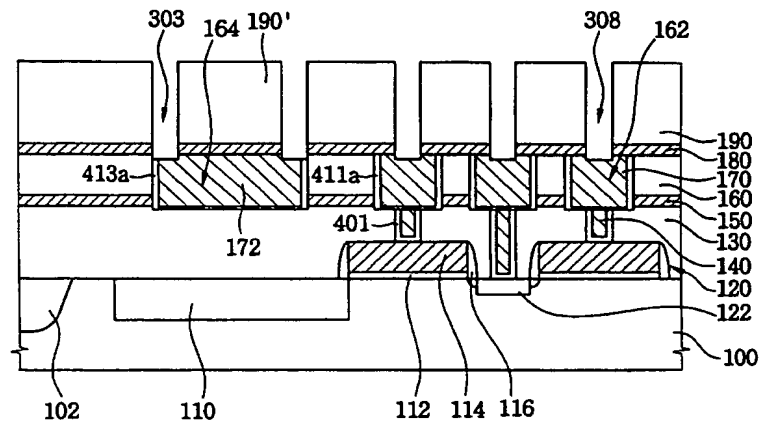


FIG. 6B

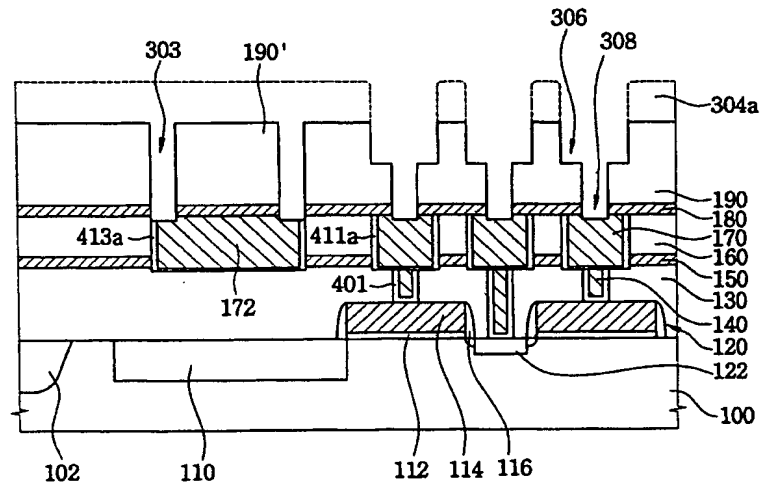


FIG. 6C

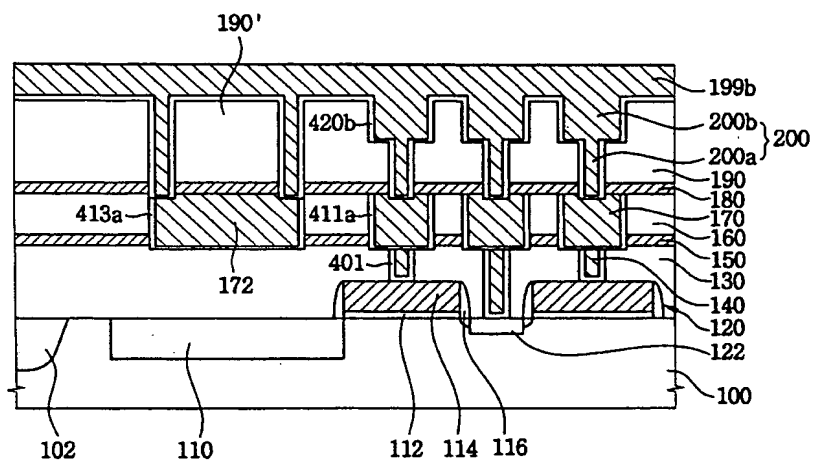


FIG. 6D

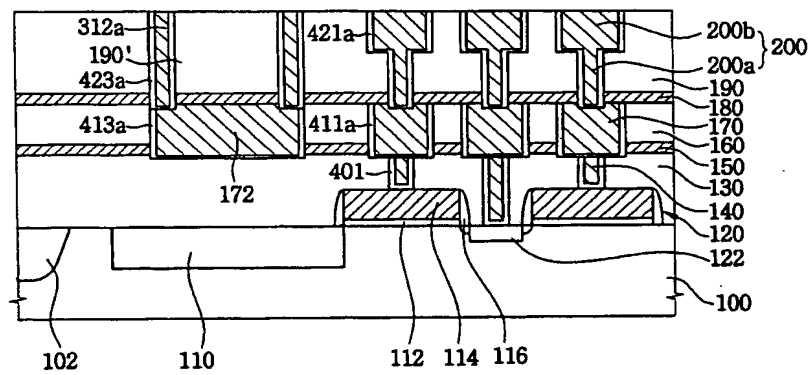




FIG. 6E

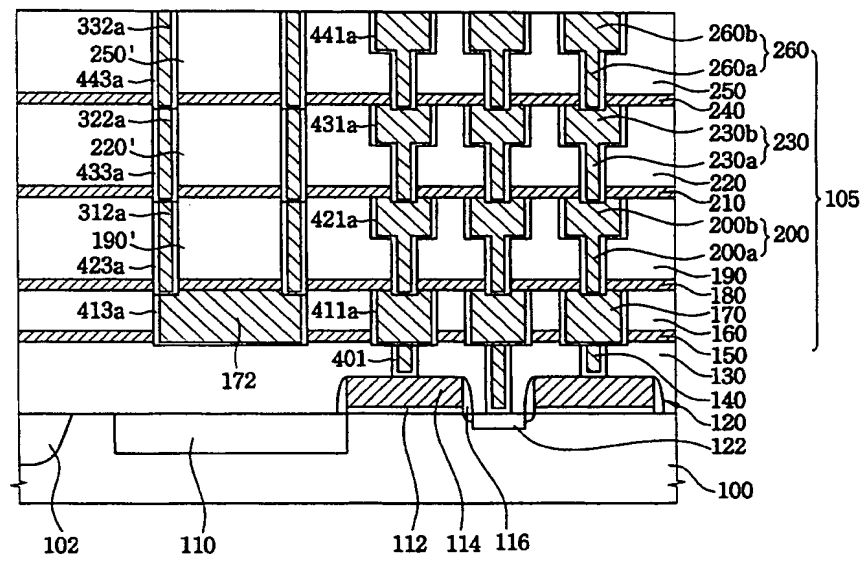


FIG. 6F

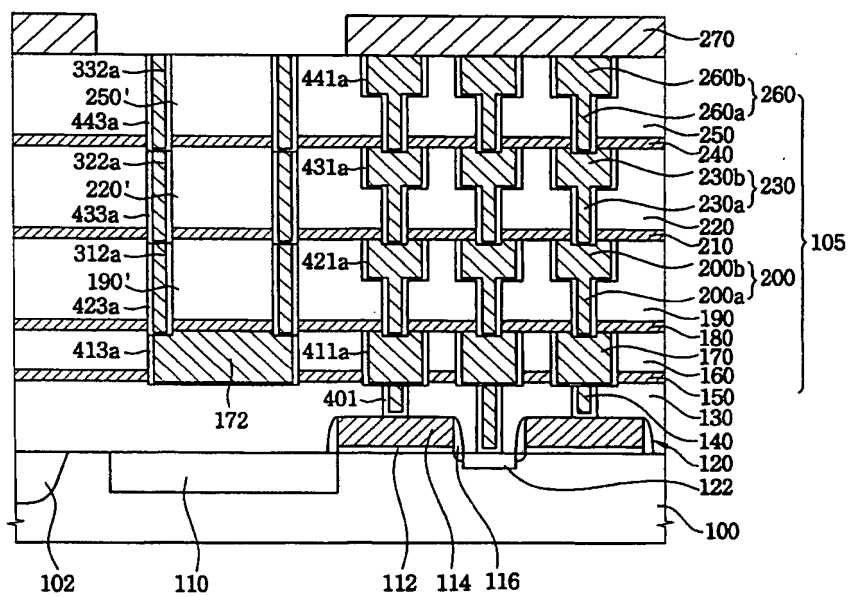


FIG. 6G

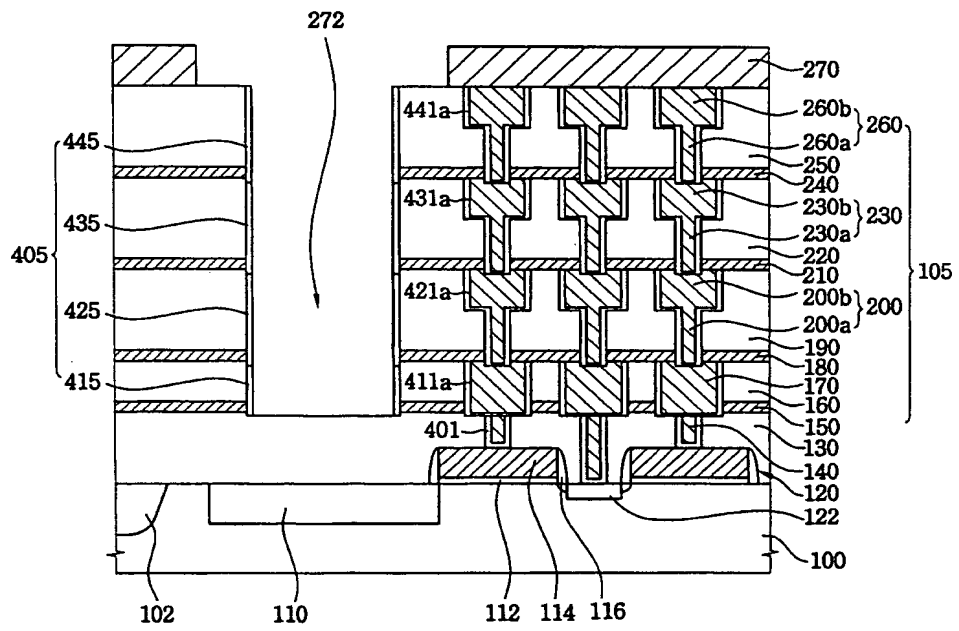


FIG. 6H

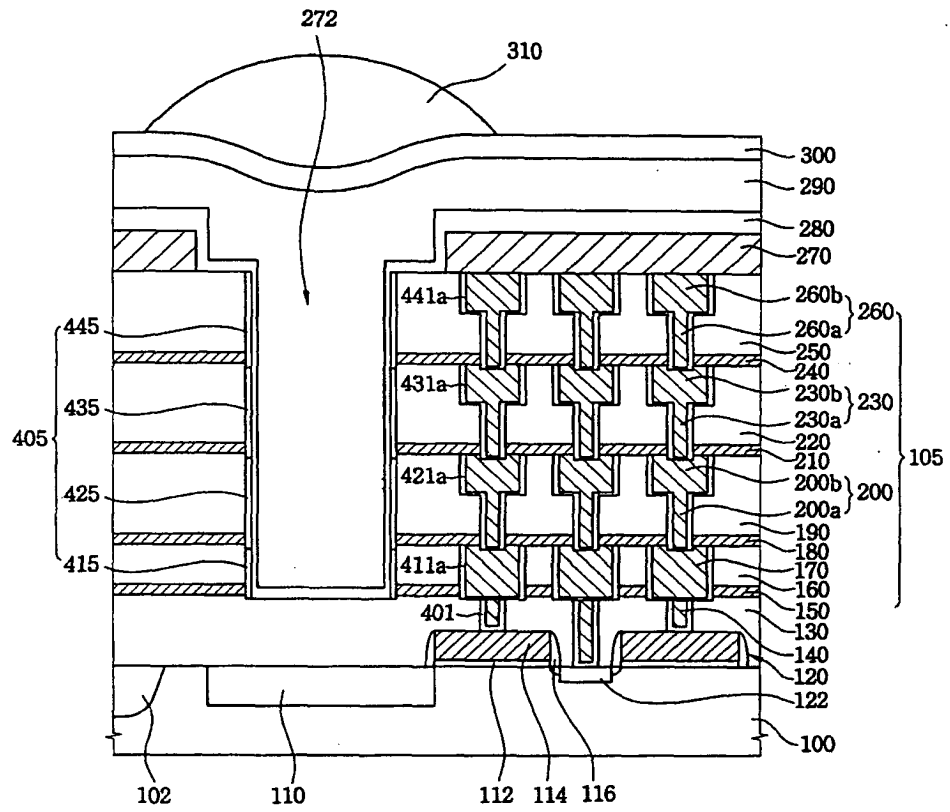


FIG. 7A

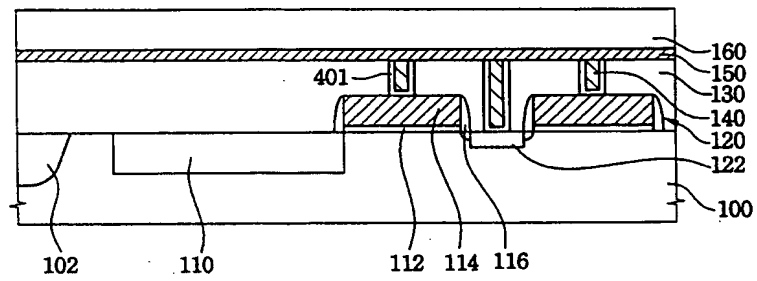


FIG. 7B

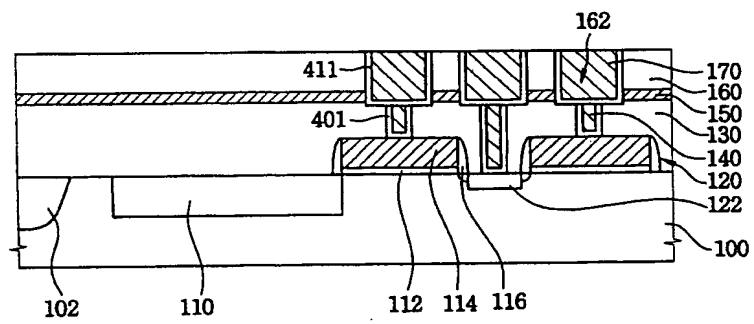


FIG. 7C

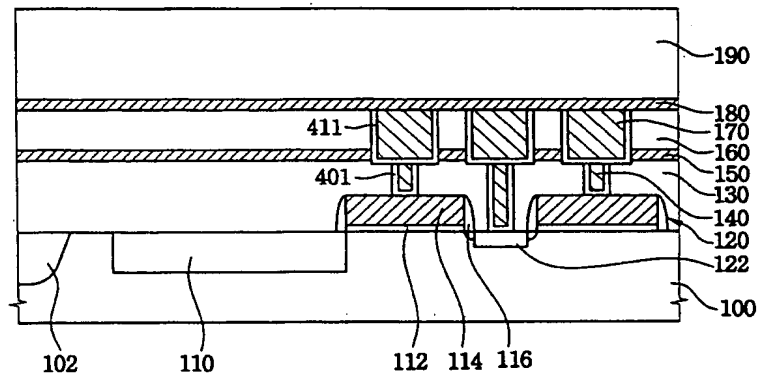


FIG. 7D

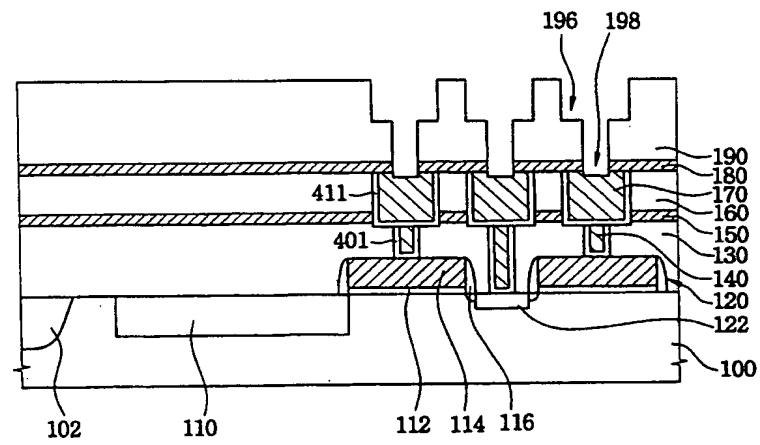


FIG. 7E

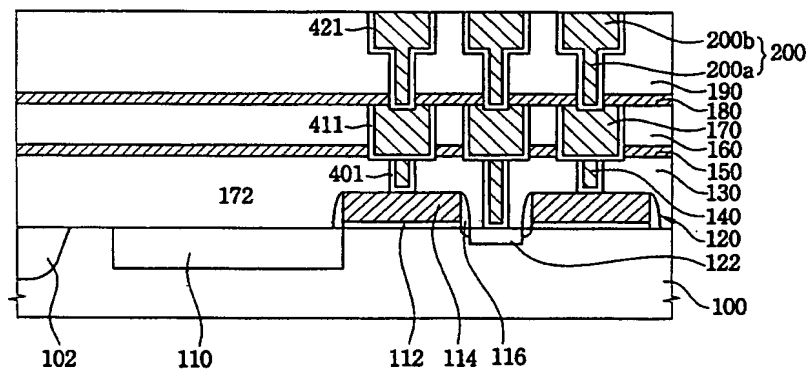


FIG. 7F

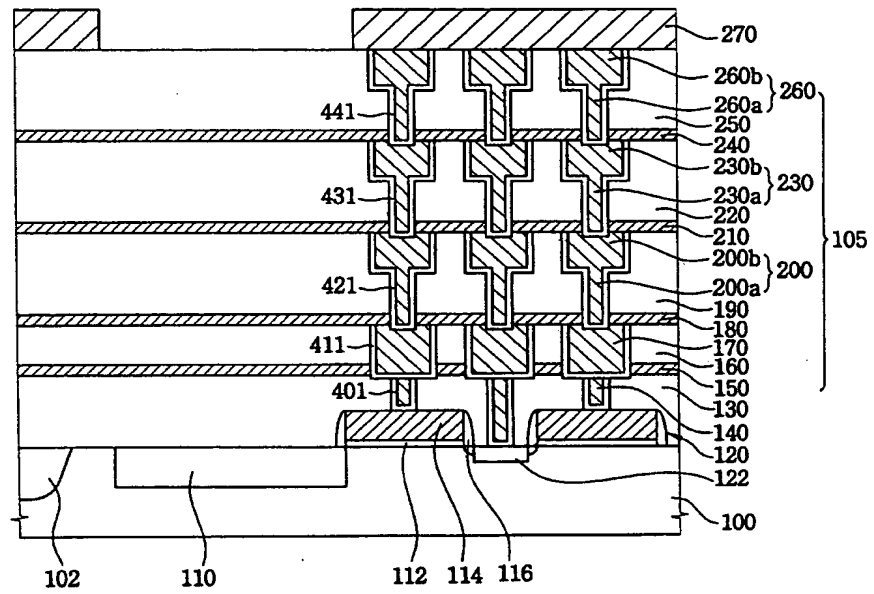




FIG. 7G

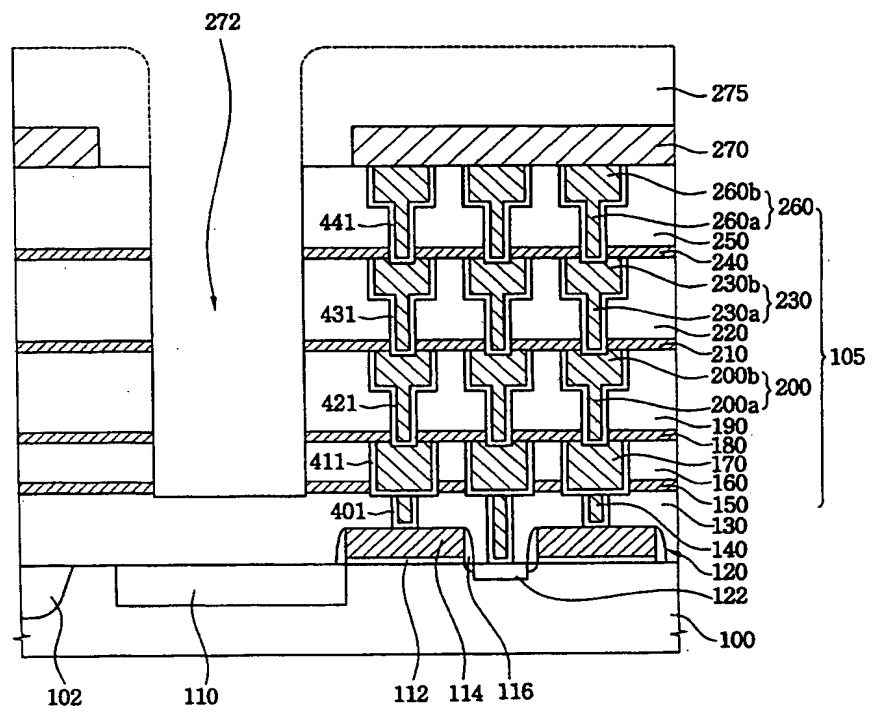


FIG. 7H

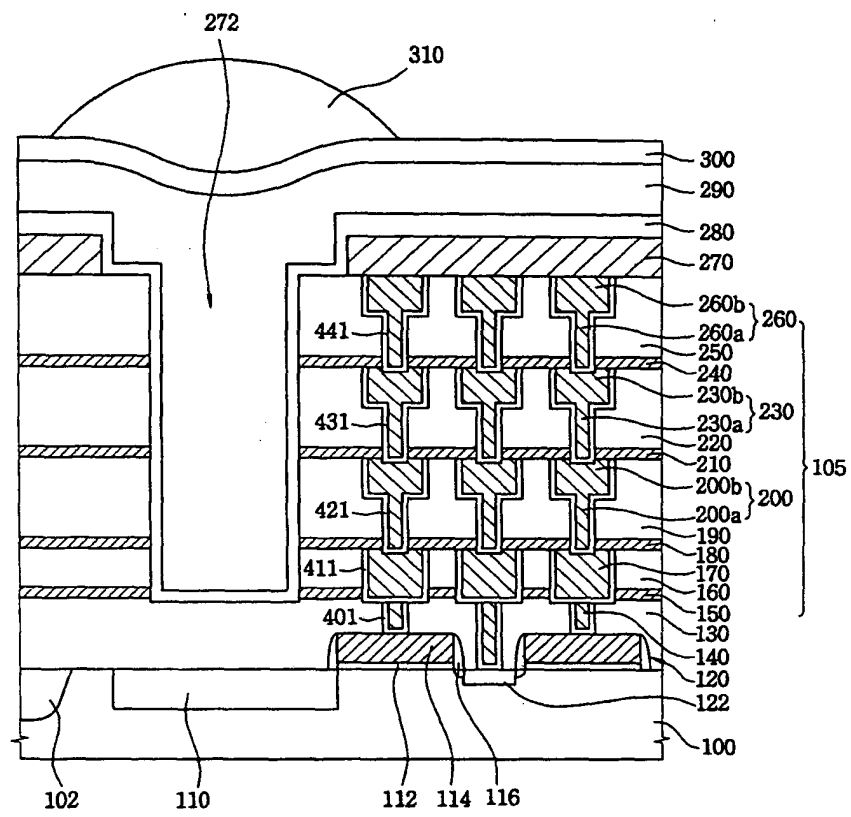


FIG. 8

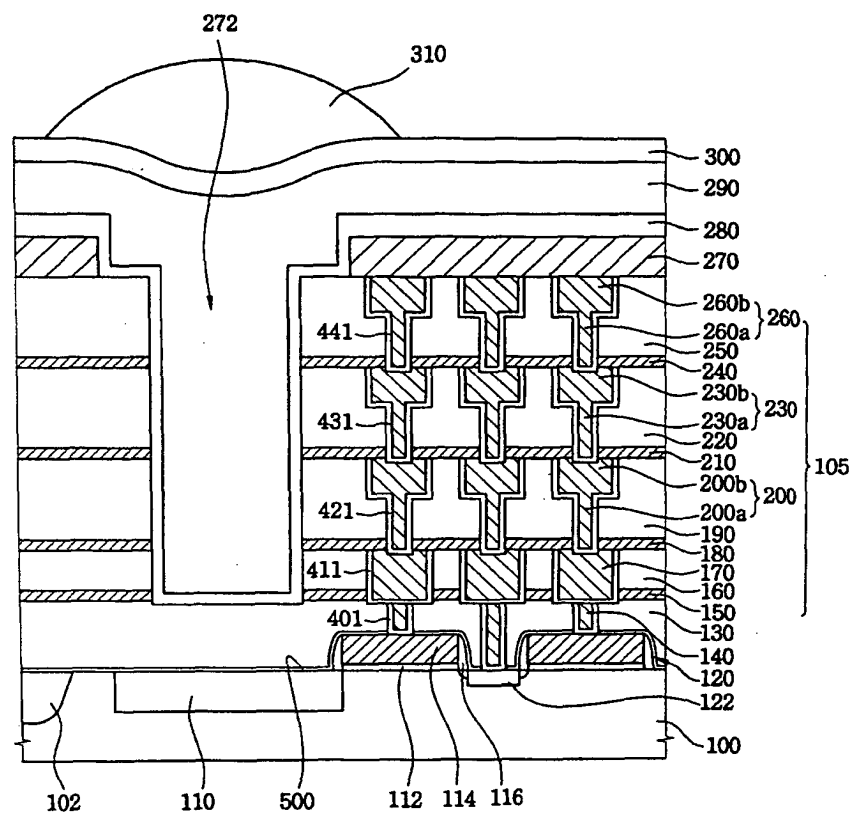


FIG. 9

